

Title (en)
METAL CHALCOGENIDE THIN LAYER ELECTRODE, METHOD FOR PRODUCTION THEREOF AND USE THEREOF

Title (de)
METALLCHALKOGENID-DÜNNSCHICHTELEKTRODE, VERFAHREN ZU IHRER HERSTELLUNG UND VERWENDUNG

Title (fr)
ÉLECTRODE À COUCHE FINE À CHALCOGÉNURE DE MÉTAL, PROCÉDÉ POUR LA PRODUCTION DE L'ÉLECTRODE ET UTILISATION ASSOCIÉE

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Application
EP 14820763 A 20141204

Priority

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Abstract (en)
[origin: WO2015082626A1] The invention relates to a method for producing a metal chalcogenide thin layer electrode, comprising the steps: (a) bringing a metal or metal oxide into contact with an elementary halogen in a non-aqueous solvent, generating a metal halogenide bond in the solution, (b) connecting a negative electrical voltage to an electrically conductive or semiconductive substrate which is in contact to the solution from step (a), and (c) during and/or after step (b), bringing the substrate into contact with an elementary chalcogen, forming a metal chalcogenide layer on the substrate. The invention furthermore relates to a metal chalcogenide thin layer electrode which can be produced by the method and use thereof as an anode for oxygen release in (photo)electrochemical water-splitting.

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Citation (search report)
See references of WO 2015082626A1

Citation (examination)

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